



# PSMNR70-40YSN

N-channel 40 V, 0.81 mOhm, 320 A standard level MOSFET in LFAK56E using NextPower-S3 Schottky-Plus technology

6 December 2023

Objective data sheet

## 1. General description

320 Amp, standard level gate drive N-channel enhancement mode MOSFET in 175 °C LFAK56E package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high performance power switching applications.

## 2. Features and benefits

- 320 A continuous  $I_{D(max)}$
- Avalanche rated, 100% tested at  $I_{AS} = 190$  A
- Low spiking, allowing for high system efficiency and low EMI designs
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery
- Low  $Q_{rr}$ , spiking, ringing, and oscillation for high system efficiency and low EMI designs
- Schottky-Plus body-diode with low  $V_{SD}$ , and low  $I_{DSS}$  leakage
- High reliability LFAK (Power SO8) package, with copper-clip and solder die attach, qualified to 175 °C
- Exposed leads for enhanced visual solder joint inspection and high-quality solder joints for ultimate reliability
- Low parasitic inductance and resistance

## 3. Applications

- High-performance synchronous rectification
- DC-to-DC converters
- High performance and high efficiency server power supply
- Brushless DC motor control
- Battery protection
- Load-switch
- eFuse

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	40	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$	[1]	-	320	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 1}$	-	-	333	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C}$	0.48	0.68	0.81	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}; V_{DS} = 32\text{ V}; V_{GS} = 10\text{ V}; T_j = 25\text{ °C}; \text{Fig. 6}$	17	57	96	nC

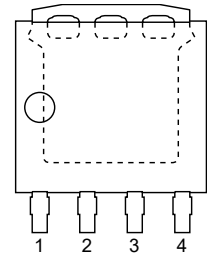
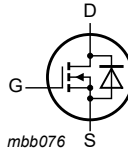
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$Q_r$	recovered charge	$I_S = 25 \text{ A}$ ; $di_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	[2]	-	[tbd]	nC

- [1] 320 A continuous current will be demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.  
 [2] includes capacitive recovery

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFPAK56E; Power-SO8 (SOT1023)</p>	 <p>mbb076 S</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMNR70-40YSN	LFPAK56E; Power-SO8	plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch	SOT1023

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMNR70-40YSN	N9040S

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).  $T_j = 25 \text{ }^\circ\text{C}$  unless otherwise stated.

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$	-	40	V
$V_{GS}$	gate-source voltage		-20	20	V
$P_{tot}$	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a>	-	333	W
$I_D$	drain current	$V_{GS} = 10 \text{ V}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$	[1]	320	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10 \text{ } \mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	1810	A
$T_{stg}$	storage temperature		-55	175	$^\circ\text{C}$

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Symbol	Parameter	Conditions	Min	Max	Unit
$T_j$	junction temperature		-55	175	°C
<b>Source-drain diode</b>					
$I_s$	source current	$T_{mb} = 25\text{ °C}$	-	100	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$	-	1810	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(i\text{nit})} = 25\text{ °C}$ ; unclamped	[2]	-	[tbd] mJ

- [1] 320 A continuous current will be demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test.

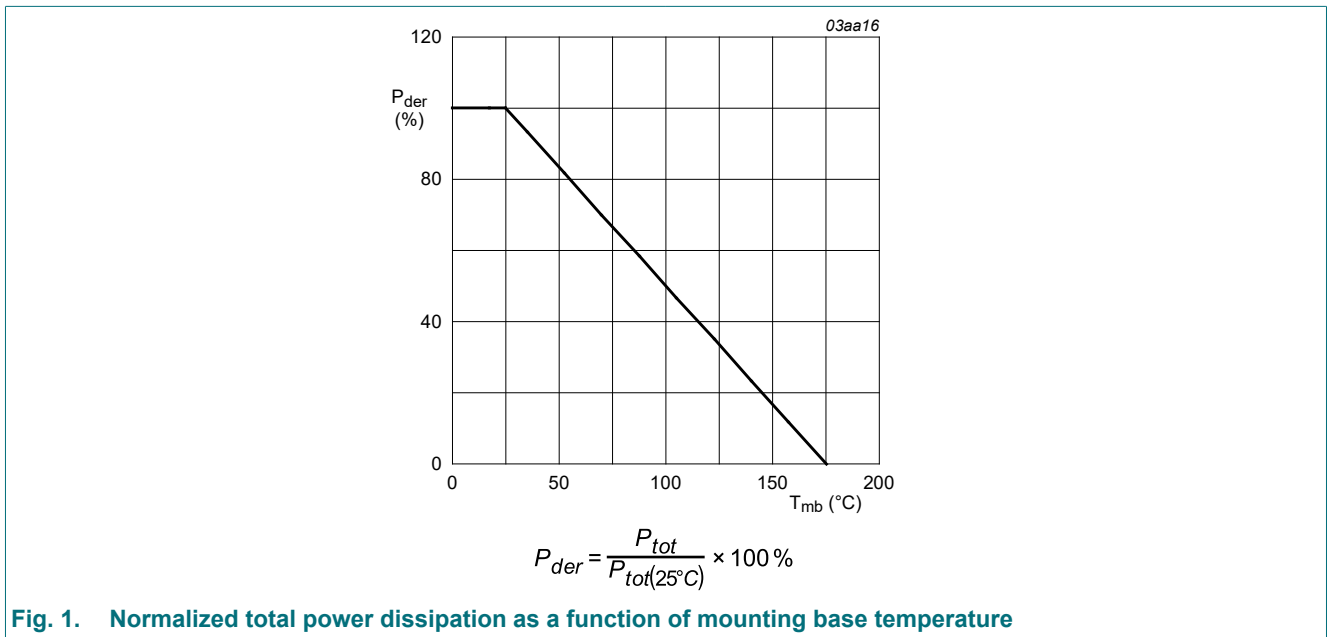


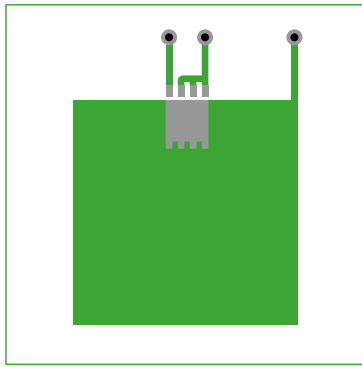
Fig. 1. Normalized total power dissipation as a function of mounting base temperature

## 9. Thermal characteristics

Table 6. Thermal characteristics

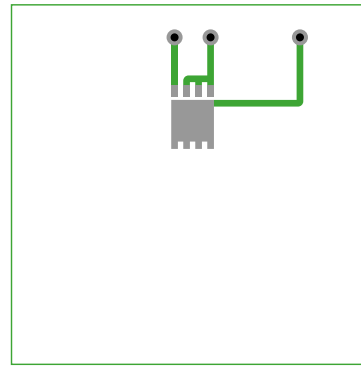
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.45	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	<a href="#">Fig. 2</a>	-	50	-	K/W
		<a href="#">Fig. 3</a>	-	125	-	K/W

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aaa-005750

Fig. 2. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper



aaa-005751

Fig. 3. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 board; 2oz copper

## 10. Characteristics

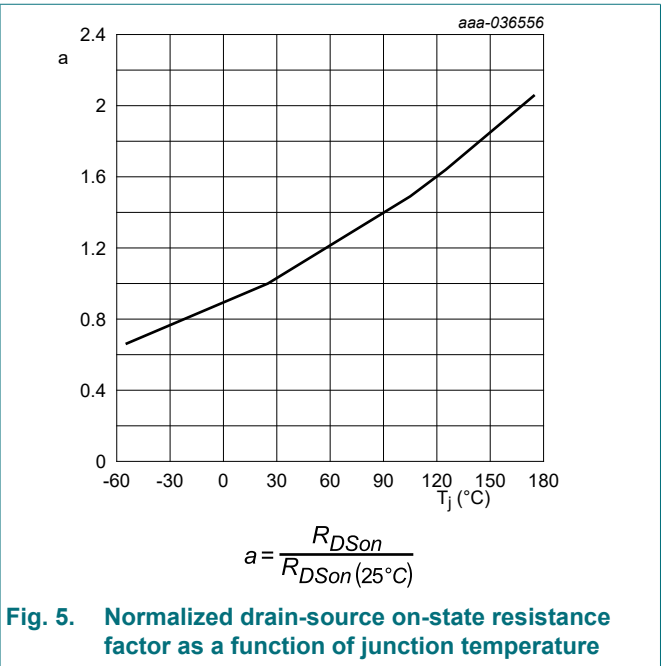
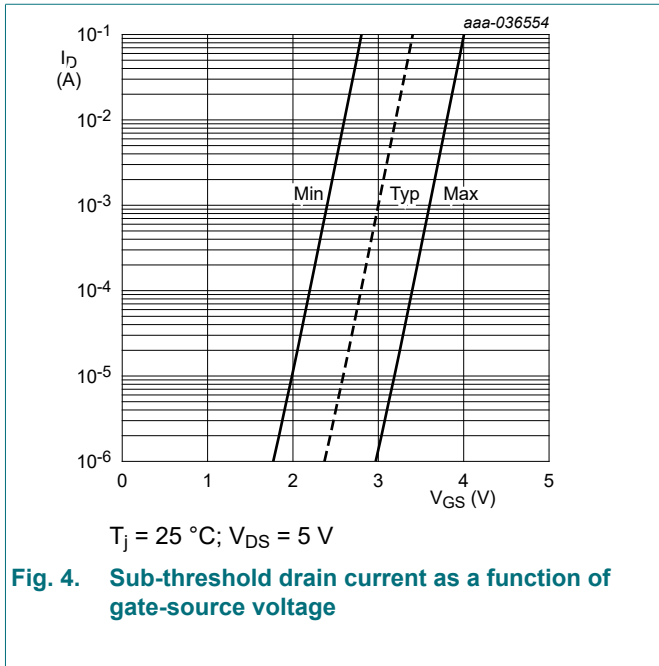
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	40	43	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 \text{ }^\circ C$	-	40	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	36	40	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C; \text{ Fig. 4}$	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$	-	-	4.3	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$	1	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	0.1	1	$\mu A$
		$V_{DS} = 16 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	1.1	10	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C$	0.48	0.68	0.81	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 105 \text{ }^\circ C; \text{ Fig. 5}$	[tbd]	[tbd]	[tbd]	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 125 \text{ }^\circ C; \text{ Fig. 5}$	[tbd]	[tbd]	[tbd]	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ C; \text{ Fig. 5}$	[tbd]	[tbd]	1.67	m $\Omega$
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	0.34	0.85	2.12	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ C; \text{ Fig. 6}$	109	182	255	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}$	-	107	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ C; \text{ Fig. 6}$	19	35	51	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		10	19	28	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		4	7.6	11	nC
$Q_{GD}$	gate-drain charge		17	57	96	nC

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25\text{ A}; V_{DS} = 32\text{ V}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 6}$	-	4.1	-	V
$C_{iss}$	input capacitance	$V_{DS} = 25\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C}$	6131	10219	14307	pF
$C_{oss}$	output capacitance		1571	2244	2917	pF
$C_{rss}$	reverse transfer capacitance		340	850	1360	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30\text{ V}; R_L = 1.2\text{ }\Omega; V_{GS} = 10\text{ V}; R_{G(ext)} = 5\text{ }\Omega; T_j = 25\text{ }^\circ\text{C}$	-	[tbd]	-	ns
$t_r$	rise time		-	[tbd]	-	ns
$t_{d(off)}$	turn-off delay time		-	[tbd]	-	ns
$t_f$	fall time		-	[tbd]	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	0.79	1	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$	-	[tbd]	-	ns
$Q_r$	recovered charge	$V_{DS} = 20\text{ V}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 7}$	[1]	[tbd]	-	nC

[1] includes capacitive recovery



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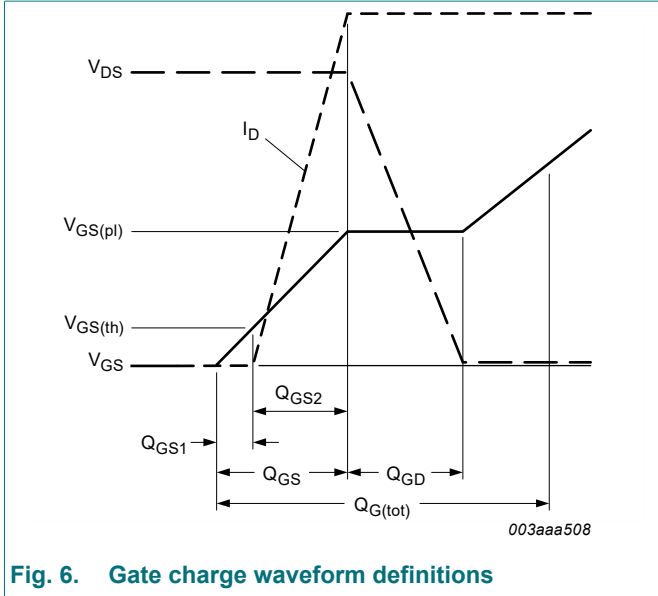


Fig. 6. Gate charge waveform definitions

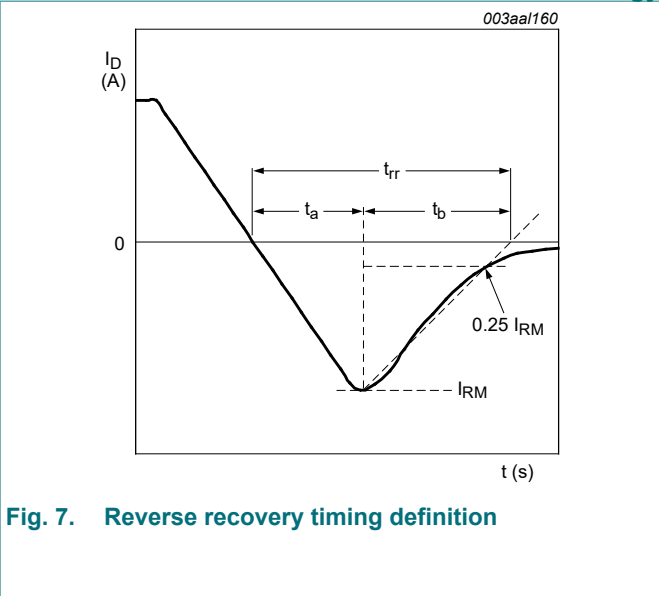


Fig. 7. Reverse recovery timing definition

11. Package outline

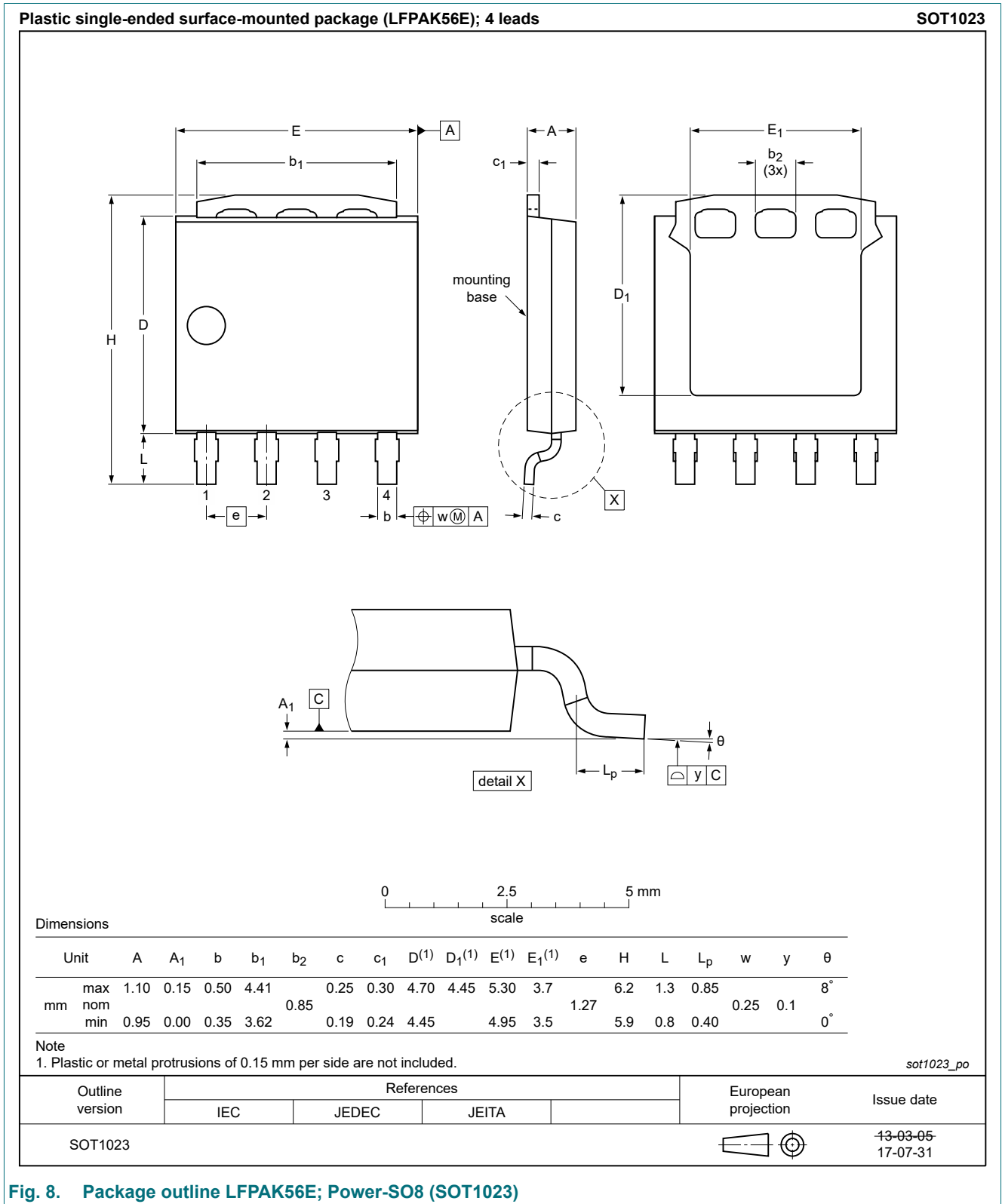


Fig. 8. Package outline LPAK56E; Power-SO8 (SOT1023)

### 12. Soldering

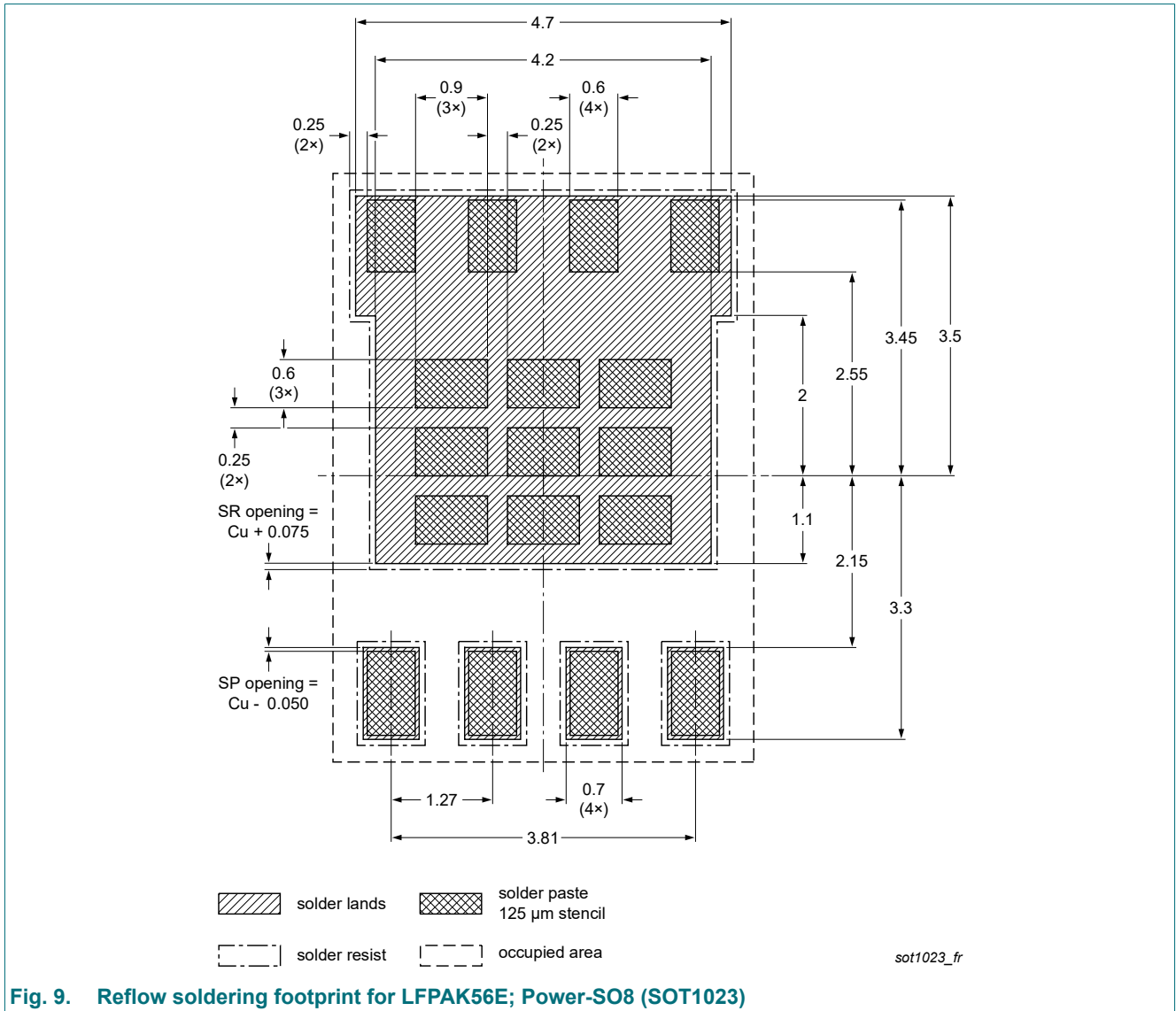


Fig. 9. Reflow soldering footprint for LPAK56E; Power-SO8 (SOT1023)



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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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